

74V2G66

PRELIMINARY DATA

DUAL BILATERAL SWITCH

- HIGH SPEED:
 trp = 0.3 ns (TYP) at Vcc = 5V
- $t_{PD} = 0.3 \text{ ns} (TYP.) \text{ at } V_{CC} = 5V$ $t_{PD} = 0.4 \text{ ns} (TYP.) \text{ at } V_{CC} = 3.3V$ • LOW POWER DISSIPATION:
- LOW POWER DISSIPATION: $I_{CC} = 1 \ \mu A \ (MAX.) at T_A = 25 \ ^{\circ}C$ • LOW "ON" RESISTANCE:
- LOW ON RESISTANCE: $R_{ON} = 10\Omega$ (TYP.) AT V_{CC} = 5.0V I_{1/O}=100µA $R_{ON} = 12\Omega$ (TYP.) AT V_{CC} = 3.3V I_{1/O}=100µA • SINE WAVE DISTORTION
- SINE WAVE DISTORTION
 0.04% (TYP.) AT V_{CC}=3.3V f=1KHz
 WIDE OPERATING VOLTAGE RANGE:
- WIDE OPERATING VOLTAGE RANGE: V_{CC} (OPR) = 2V to 5V

DESCRIPTION

The 74V2G66 is an high-speed CMOS DUAL BILATERAL SWITCH fabricated in silicon gate C2MOS technology. It achieves high speed propagation delay and VERY LOW ON resistances while maintaining true CMOS low power consumption. This feature makes this part ideal for battery-powered equipment. This bilateral switch handles rail to rail analog and digital signals that may vary across the full

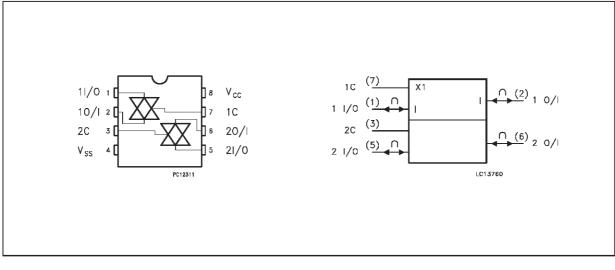


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PACKAGE	TUBE	T & R					
SOT23-8L		74V2G66STR					

power-supply range (from Vcc to Ground).

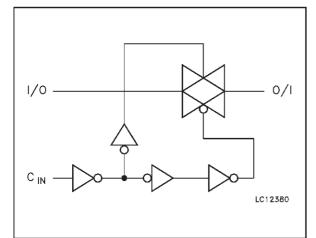
The C input is provided to control the switch and it's compatible with standard CMOS output; the switch is ON when the C input is held high and off when C is held low. It can be used in many application as Battery Powered System, Audio Signal Routing, Communications System, Test Equipment. It's available in the commercial temperature range in SOT23-8L.

PIN CONNECTION AND IEC LOGIC SYMBOLS



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LOGIC DIAGRAM



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 5	1 to 2 I/O	Independent Input/Output
2, 6	1 to 2 O/I	Independent Output/Input
3, 7	1C to 2C	Enable Input (Active HIGH)
4	GND	Ground (0V)
8	V _{CC}	Positive Supply Voltage

TRUTH TABLE

CONTROL	SWITCH FUNCTION			
Н	ON			
L	OFF			

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage	-0.5 to +7	V
VI	DC Input Voltage	-0.5 to V _{CC} + 0.5	V
V _{IC}	DC Control Input Voltage	-0.5 to 7	V
Vo	DC Output Voltage	-0.5 to V _{CC} + 0.5	V
I _{IK}	DC Input Diode Current	± 20	mA
I _{IK}	DC Control Input Diode Current	- 20	mA
I _{OK}	DC Output Diode Current	± 20	mA
lo	DC Output Current	± 50	mA
I _{CC} or I _{GND}	DC V _{CC} or Ground Current	± 100	mA
T _{stg}	Storage Temperature	-65 to +150	°C
TL	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these condition is not implied.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V _{CC}	Supply Voltage (note 1)	2 to 5.5	V
VI	Input Voltage	0 to V _{CC}	V
V _{IC}	Control Input Voltage	0 to 5.5	V
Vo	Output Voltage	0 to V _{CC}	V
T _{op}	Operating Temperature:	-40 to +85	°C
dt/dv	Input Rise and Fall Time (note 2)	0 to 10	ns/V

1) Truth Table guaranteed: 1.2V to 5.5V 2) V_{IN} from 30% to 70% V_{CC}

DC SPECIFICATIONS

Symbol	Parameter	Test Conditions		Value					Unit
		Vcc		$T_{A} = 25 \ ^{\circ}C$			-40 to 85 °C		
		(V)		Min.	Тур.	Max.	Min.	Max.	
VIH	High Level Control Input	2.0		1.5			1.5		
	Voltage	2.7 to 5.5		0.7V _{CC}			0.7V _{CC}		V
VIL	Low Level Control Input	2.0				0.5		0.5	
	Voltage	2.7 to 5.5				0.3V _{CC}		0.3V _{CC}	V
R _{ON}	ON Resistance	3.3 ^(**)	$V_{IC} = V_{IH}$		14	26		30	
		5.0 ^(*)	$V_{I/O} = V_{CC}$ to GND $I_{I/O} \le 1$ mA		12	17		20	Ω
		3.3 ^(**)	$V_{IC} = V_{IH}$		12	18		24	
		5.0 ^(*)	$V_{I/O} = V_{CC} \text{ or GND}$ $I_{I/O} \le 1 \text{mA}$		10	14		18	
ΔR_{ON}	Difference of ON Resistance Between Switches	3.0 to 5.5	$\begin{array}{c} V_{IC} = V_{IH} \\ V_{I/O} = V_{CC} \text{ to GND} \\ I_{I/O} \leq 1 \text{mA} \end{array}$		2	0			Ω
I _{OFF}	Input/Output Leakage Current (SWITCH OFF)	5.5	$V_{OS} = V_{CC} \text{ to } GND$ $V_{IS} = V_{CC} \text{ to } GND$ $V_{IC} = V_{IL}$. <u>%</u>	34.12	±0.1		±1.0	μΑ
I _{IZ}	Switch Input Leakage Current (SWITCH ON, OUTPUT OPEN)	5.5	$V_{OS} = V_{CC} \text{ to GND}$ $V_{IC} = V_{IH}$	30	m.	±0.1		±1.0	μΑ
I _{IN}	Control Input Leakage Current	0 to 5.5	$V_{IC} = 5.5V \text{ or } GND$			±0.1		±1.0	μΑ
Icc	Quiescent Supply Current	5.5	$V_{IC} = V_{CC}$ or GND			1		10	μA
	ange is 5V ± 0.5V range is 3.3V ± 0.3V								

Symbol	Parameter	Те	st Condition	Value				Unit	
		Vcc	Vcc		T _A = 25 °C		-40 to 85 °C		
		(V)		Min.	Тур.	Max.	Min.	Max.	
t _{PD}	Delay Time	3.3 ^(*)	$t_r = t_f = 6ns$		0.4	0.8		1.2	ne
		5.0 ^(**)	$t_r = t_f = 0.05$		0.3	0.6		1.0	ns
t _{PZL}	Output Enable Time	3.3(*)	$R_{\rm I} = 1 k \Omega$		2.5	4.0		5.0	ns
t _{PZH}		5.0 ^(**)	11 - 182		2.0	4.0		5.0	115
t _{PLZ}	Output Disable Time	3.3(*)	$R_1 = 500\Omega$		5.0	7.5		9.0	20
t _{PHZ}		5.0 ^(**)	$K_{L} = 50022$		5.0	7.5		9.0	ns
C _{IN}	Input Capacitance				5				рF
C _{I/O}	Switch Terminal Capacitance				10				pF
CPD	Power Dissipation	3.3			2.5				pF
	Capacitance (note 1)	5.0			3				

AC ELECTRICAL CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input $t_r = t_f = 3 \text{ ns}$)

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. $I_{CC}(opr) = C_{PD} \bullet V_{CC} \bullet f_{IN} + I_{CC}/2$ (switch). (*) Voltage range is 3.3V \pm 0.3V

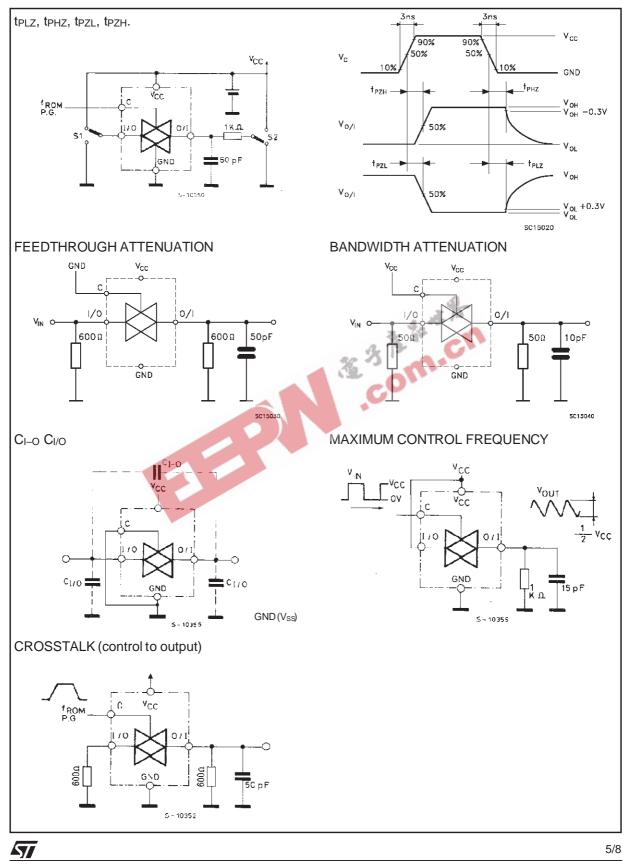
(**) Voltage range is $5V \pm 0.5V$

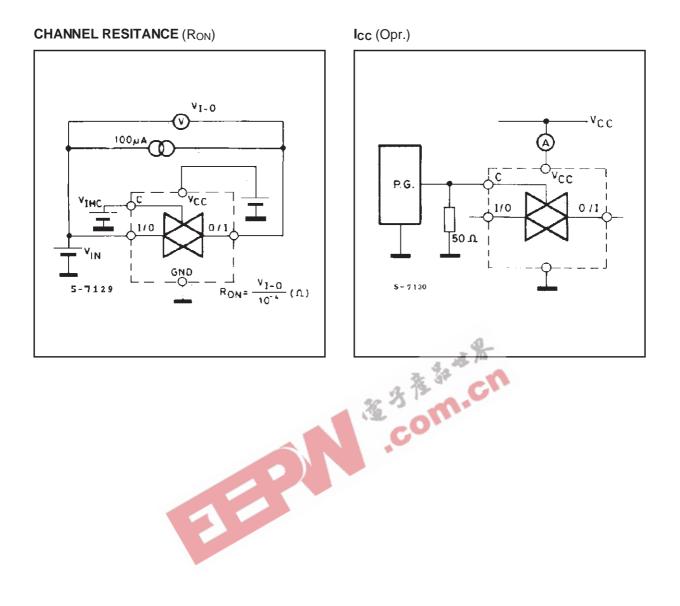
ANALOG SWITCH CHARACTERISTICS (GND = 0 V, T_A = 25°C)

Symbol	Parameter		Test Condition	Value	Unit
		V cc (∀)	V _{IN} (Vp-p)		
	Sine Wave Distortion	3.3	2.75 $f_{IN} = 1 \text{ KHz}$ $R_L = 10 \text{K}\Omega$ $C_L = 50 \text{ pF}$	0.04	%
	(THD)	5.0 ^(*)	4	0.04	
f _{MAX}	Frequency Response	3.3	Adjust fin voltage to Obtain 0dBm at Vos.	150	MHz
	(Switch ON)	5.0(*)	Increase f_{IN} Frequency until dB Meter reads -3dB R _L = 50 Ω , C _L = 10pF	180	
	Feedthrough	3.3	V_{IN} is centered at $V_{CC}/2$.		dB
	Attenuation (Switch OFF)	5.0 ^(*)	Adjust f_{IN} voltage to obtain 0dBm at V_{IS} R _L = 600 Ω , C _L = 50pF, f_{IN} = 1MHz sine wave	-60	
	Crosstalk (Control	3.3	$R_L = 600\Omega$, $C_L = 50pF$, $f_{IN} = 1MHz$ square wave	60	mV
	Input to Signal Output)	5.0 ^(*)	$t_r = t_f = 6ns$	60	
	Crosstalk (Between	3.3	$R_L = 600\Omega$, $C_L = 50pF$, $f_{IN} = 1MHz$ sine wave	-60	dB
	Switches)	5.0 ^(*)		-60	

(*) Voltage range is $5V \pm 0.5V$

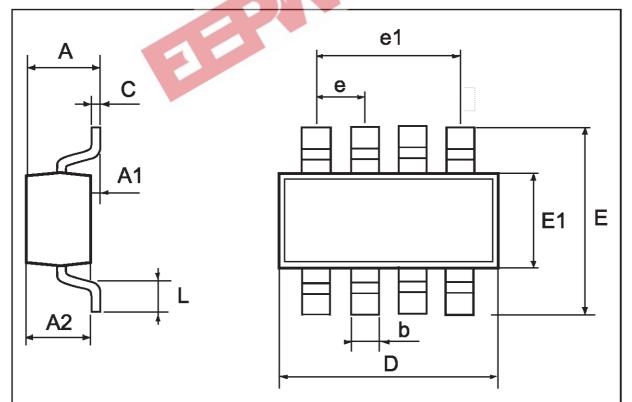
SWITCHING CHARACTERISTICS TEST CIRCUIT





DIM.		mm		mils		
2	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
А	0.90		1.45	35.4		57.1
A1	0.00		0.15	0.0		5.9
A2	0.90		1.30	35.4		51.2
b	0.22		0.38	8.6		14.9
С	0.09		0.20	3.5		7.8
D	2.80		3.00	110.2		118.1
E	2.60		3.00	102.3	0	118.1
E1	1.50		1.75	59.0	*	68.8
L	0.35		0.55	13.8	cn	21.6
е		0.65	3	om.	25.6	
e1		1.95			76.7	

SOT23-8L MECHANICAL DATA





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